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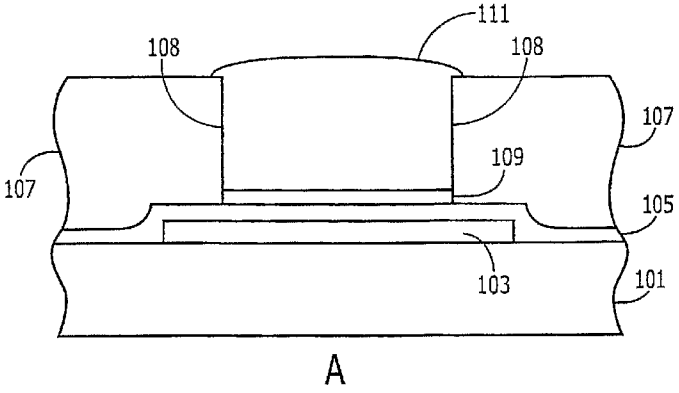
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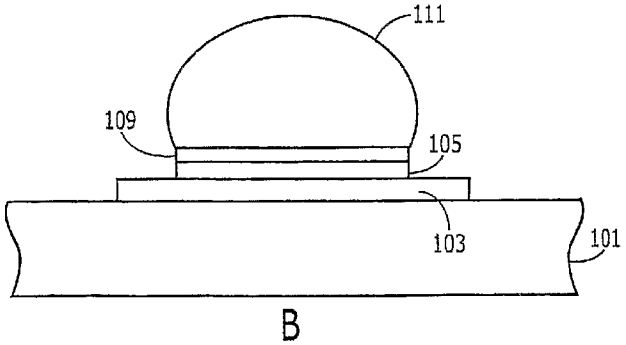
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(54) Title: METHODS OF FORMING SOLDER BUMPS ON EXPOSED METAL PADS AND RELATED STRUCTURES



A



B

(57) Abstract: A method of forming an electronic structure may include providing a substrate having a metal pad thereon. A conductive barrier layer may be formed on a first portion of the metal pad, and a second exposed portion of the metal pad may be free of the conductive barrier layer. In addition, an interconnection structure may be provided on the conductive barrier layer with the conductive barrier layer being between the interconnection structure and the metal pad. Moreover, the interconnection structure and the conductive barrier layer may include different materials. Related structures are also discussed.

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